

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: ZVN4210GTA
Manufacturer: Diodes Incorporated
Package: Please confirm with sales
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/diodes-incorporated/zvn4210gta.html>

Request a Quote:

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Contact Information

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

SOT223 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET
Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D $T_A = +25^\circ C$
100V	1.5Ω @ $V_{GS} = 10V$	800mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications

Features and Benefits

- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>

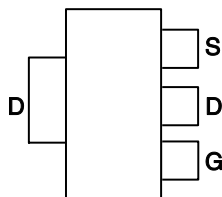
Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (Approximate)

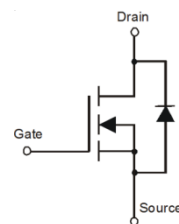
SOT223(Type DN)



Top View



Pin Out - Top View

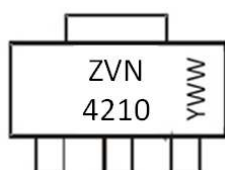


Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
ZVN4210GTA	SOT223 (Type DN)	1,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>

Marking Information


ZVN4210 = Product Type Marking Code
 YWW = Date Code Marking
 Y or $\bar{Y}$ = Year (ex: 1 = 2021)
 WW or $\bar{WW}$ = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current $V_{GS} = 10\text{V}$	I_D	800	mA
Pulsed Drain Current	I_{DM}	6	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

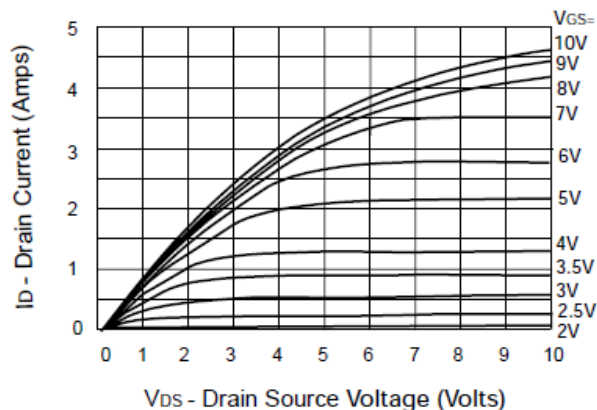
Characteristic	Symbol	Value	Unit
Total Power Dissipation	P_D	2	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

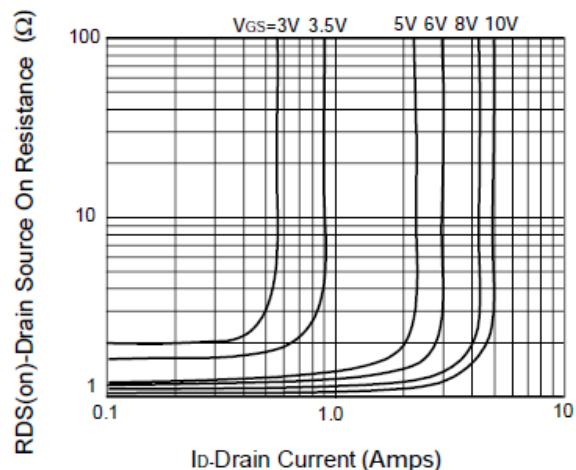
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10	μA	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$
		—	—	100	μA	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}, T = 125^\circ\text{C}$ (Note 6)
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	—	2.4	V	$V_{DS} = V_{GS}, I_D = 1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	1.5	Ω	$V_{GS} = 10\text{V}, I_D = 1.5\text{A}$
		—	—	1.8	Ω	$V_{GS} = 5\text{V}, I_D = 0.5\text{A}$
Diode Forward Voltage (Note 5)	V_{SD}	—	0.79	—	V	$I_S = 0.32\text{A}, V_{GS} = 0\text{V}$
		—	0.89	—	V	$I_S = 1.0\text{A}, V_{GS} = 0\text{V}$
On-State Drain Current (Note 5)	$I_{D(on)}$	2.5	—	—	A	$V_{DS} = 25\text{V}, V_{GS} = 10\text{V}$
Forward Transconductance (Notes 5, 6)	g_{fs}	250	—	—	mS	$V_{DS} = 25\text{V}, I_D = 1.5\text{A}$
Reverse Recovery Time (to $I_R = 10\%$)	t_{RR}	—	135	—	ns	$I_F = 0.45\text{A}, V_{GS} = 0\text{V}, I_R = 100\text{mA}, V_R = 10\text{V}$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	—	—	100	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	—	40	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	12	pF	
Turn-On Delay Time (Note 7)	$t_{D(on)}$	—	—	4	ns	$V_{DD} = 25\text{V}, I_D = 1.5\text{A}$
Turn-On Rise Time (Note 7)	t_R	—	—	8	ns	
Turn-Off Delay Time (Note 7)	$t_{D(off)}$	—	—	20	ns	
Turn-Off Fall Time (Note 7)	t_F	—	—	30	ns	

- Notes:
5. Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
 6. Sample test.
 7. Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator. Spice parameter data is available upon request for this device

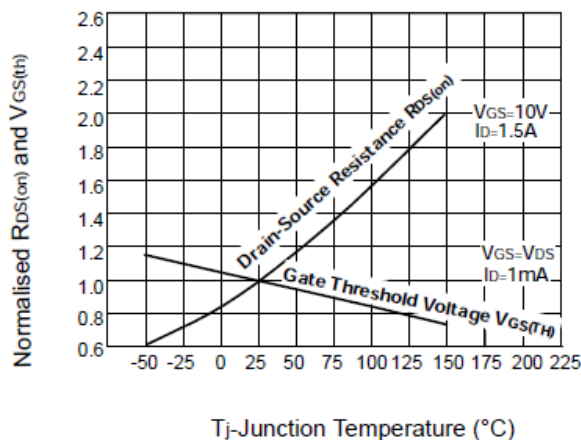
Electrical Characteristics



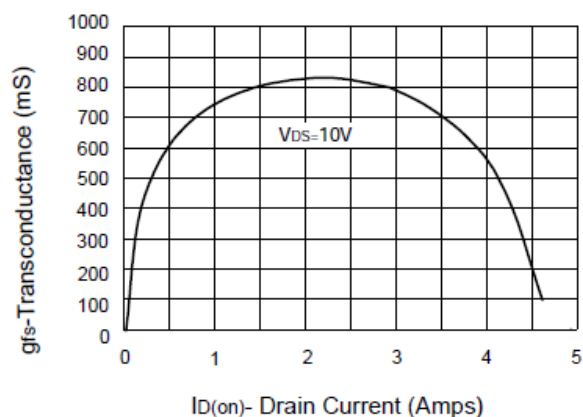
Saturation Characteristics



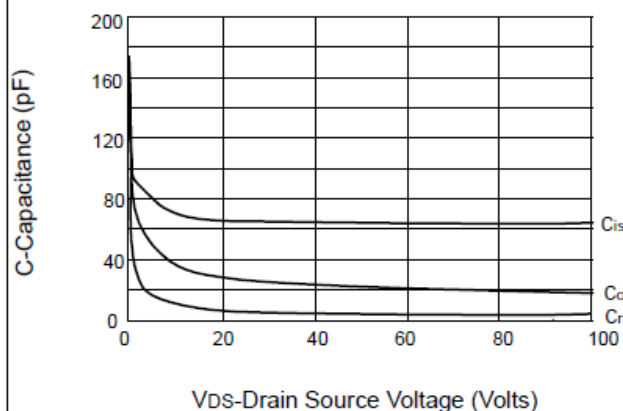
On-resistance v drain current



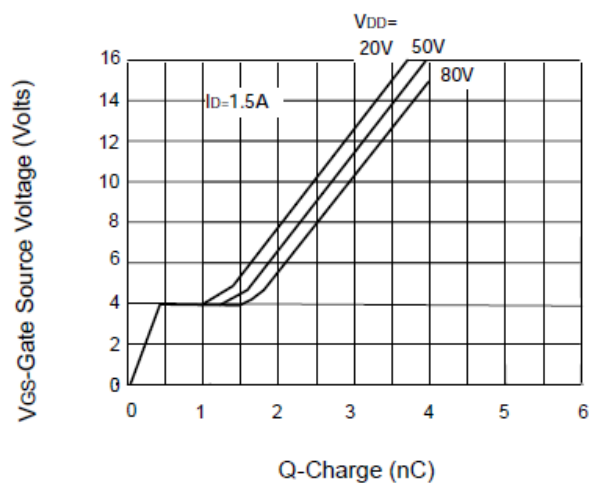
Normalised RDS(on) and VGS(th) v Temperature



Transconductance v drain current



Capacitance v drain-source voltage

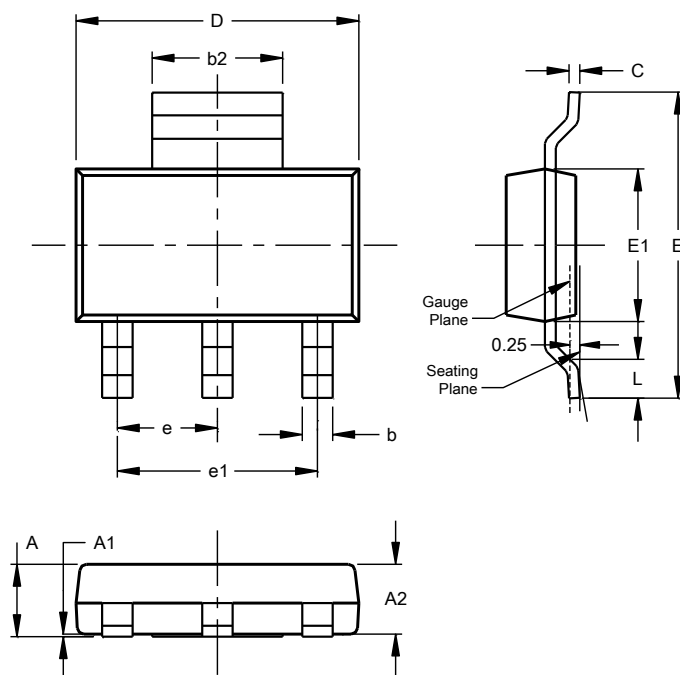


Gate charge v gate-source voltage

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

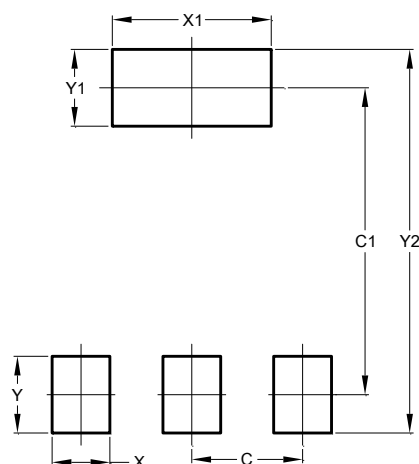


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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